

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, g}	Q _g (Typ.)
30	0.0075 at V _{GS} = 10 V	35	10.2 nC
	0.0098 at V _{GS} = 4.5 V	35	

FEATURES

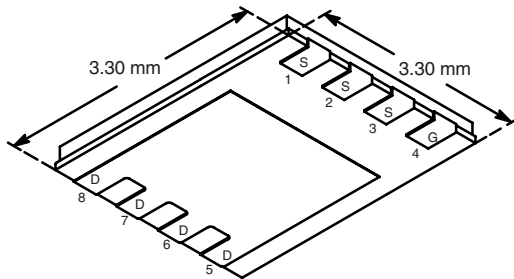
- Halogen-free
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested



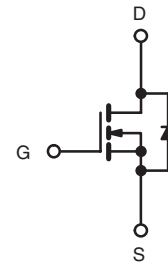
APPLICATIONS

- Synchronous Rectification

PowerPAK[®] 1212-8



Bottom View



N-Channel MOSFET

Ordering Information: Si7114ADN-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	35 ^g	A
		T _C = 70 °C	35 ^g	
		T _A = 25 °C	18 ^{b, c}	
		T _A = 70 °C	14.5 ^{b, c}	
Pulsed Drain Current	I _{DM}	60		
Avalanche Current	L = 0.1 mH	I _{AS}	30	mJ
Avalanche Energy		E _{AS}	45	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	32	A
		T _A = 25 °C	3.2 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	39	W
		T _C = 70 °C	25	
		T _A = 25 °C	3.7 ^{b, c}	
		T _A = 70 °C	2.4 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	26	34	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	2.4	3.2	

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK 1212 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 81 °C/W.
- Package limited.

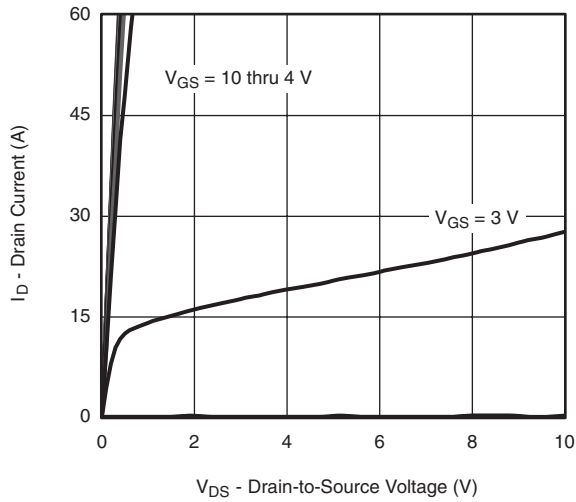
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		33		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 18\text{ A}$		0.0062	0.0075	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 16\text{ A}$		0.0081	0.0098	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 18\text{ A}$		50		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1230		pF
Output Capacitance	C_{oss}			275		
Reverse Transfer Capacitance	C_{rss}			105		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 19\text{ A}$		21	32	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 19\text{ A}$		10.2	20	
Gate-Drain Charge	Q_{gd}			3.9		
Gate Resistance	R_g		$f = 1\text{ MHz}$	0.3	1.6	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		20	30	ns
Rise Time	t_r			14	21	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		11	20	
Rise Time	t_r			8	16	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			7	14	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			32	A
Pulse Diode Forward Current	I_{SM}				60	
Body Diode Voltage	V_{SD}	$I_S = 10\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		24	36	ns
Body Diode Reverse Recovery Charge	Q_{rr}			20	30	nC
Reverse Recovery Fall Time	t_a			16		ns
Reverse Recovery Rise Time	t_b			8		

Notes:

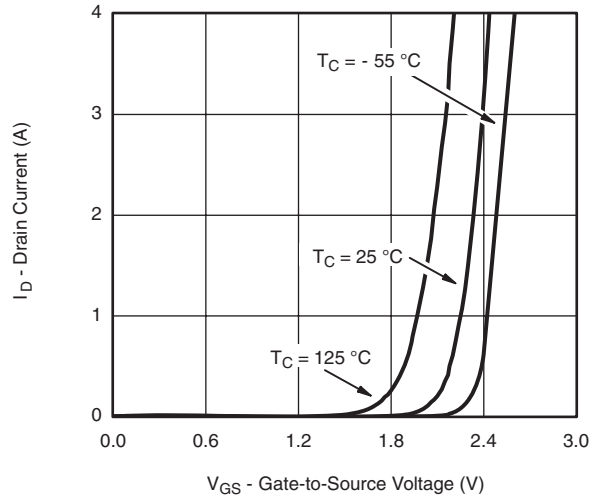
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

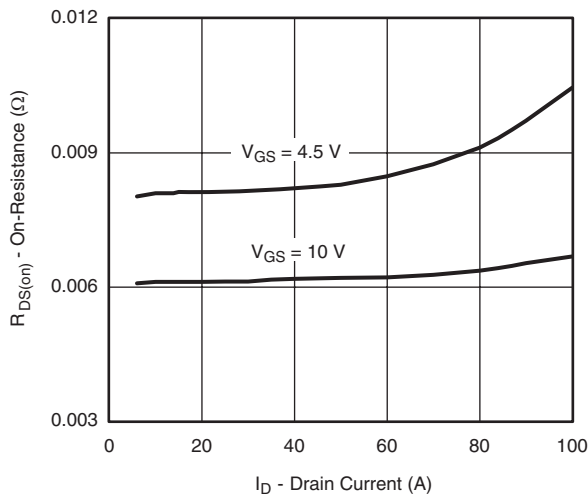
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



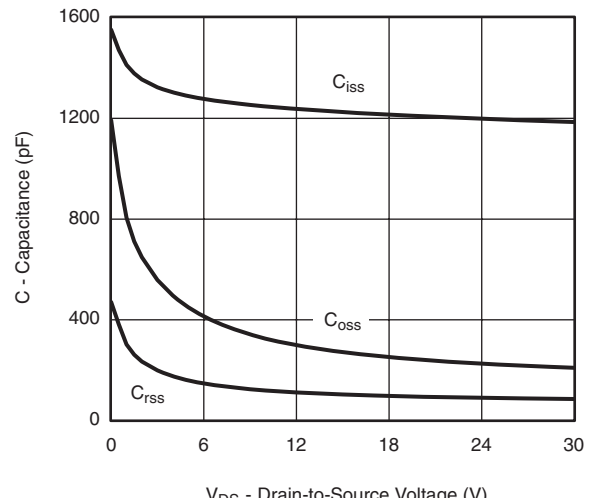
Output Characteristics



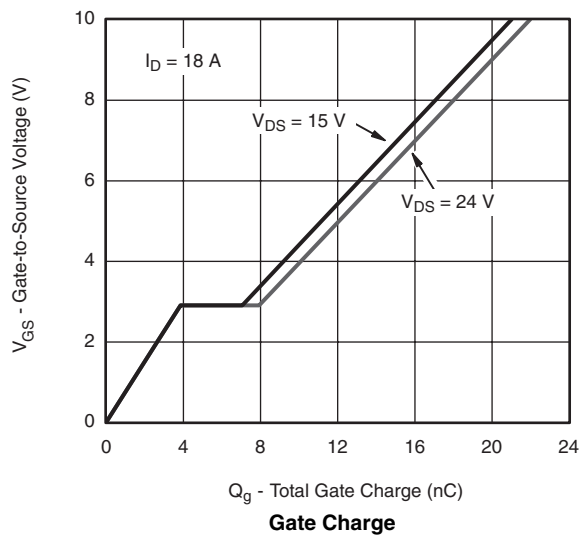
Transfer Characteristics



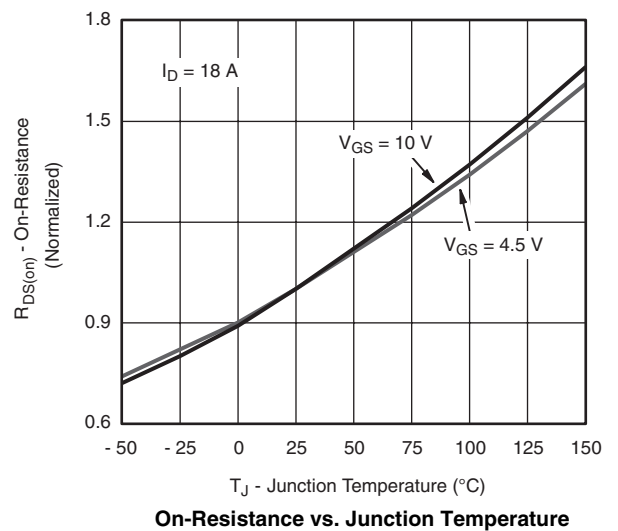
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

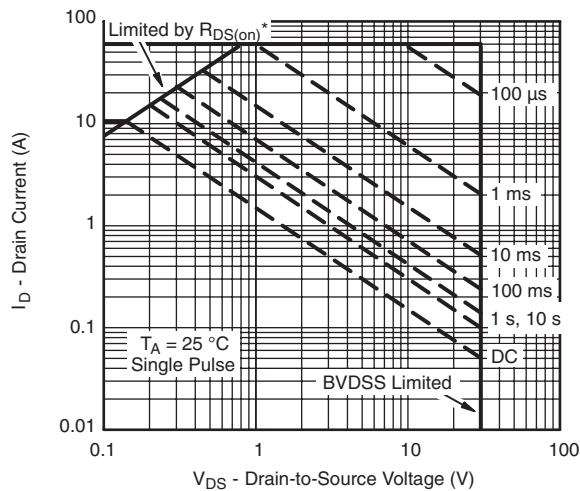
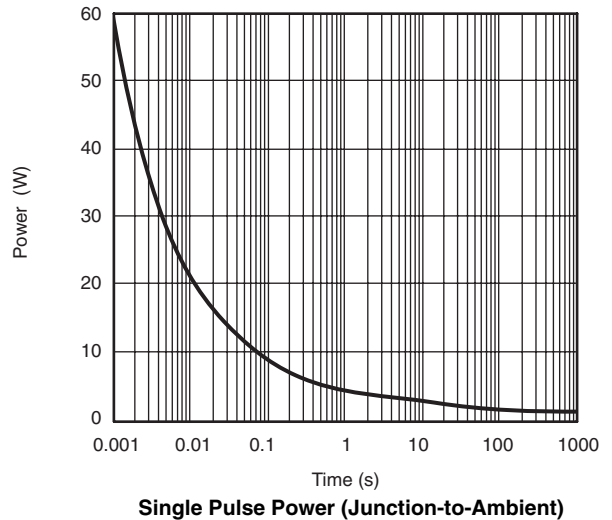
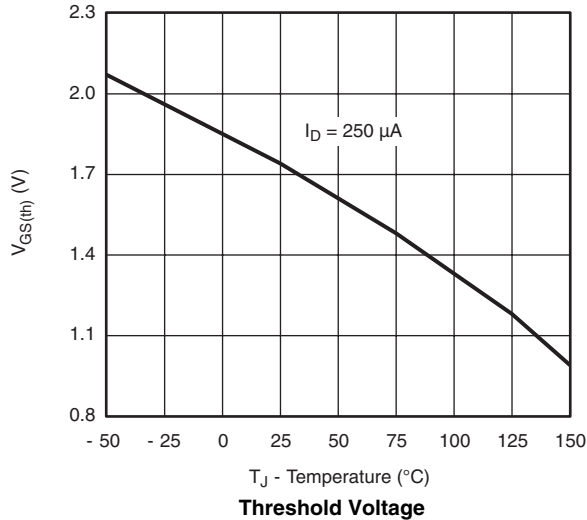
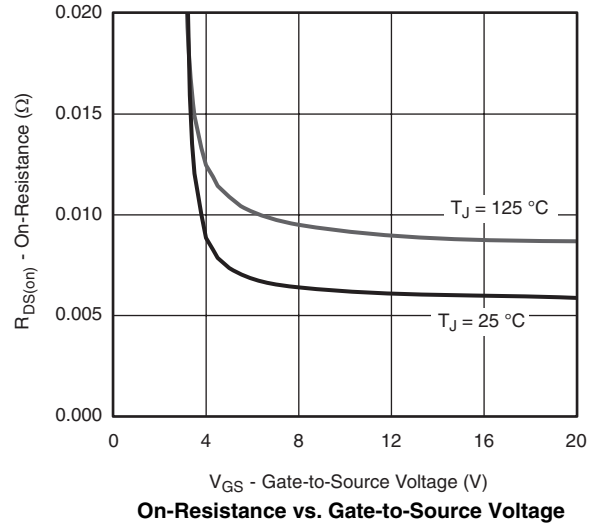
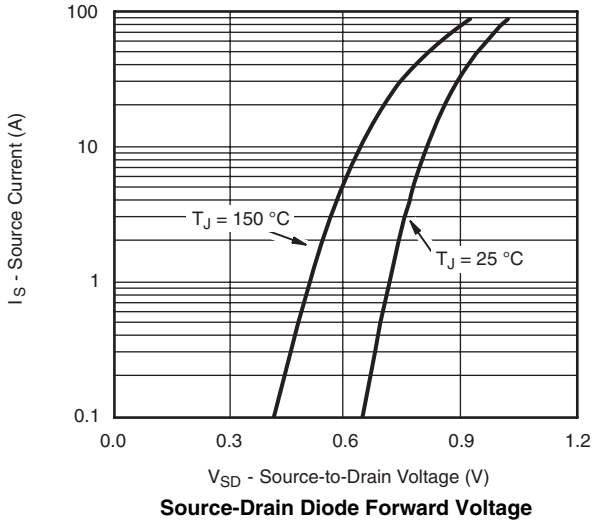


Gate Charge



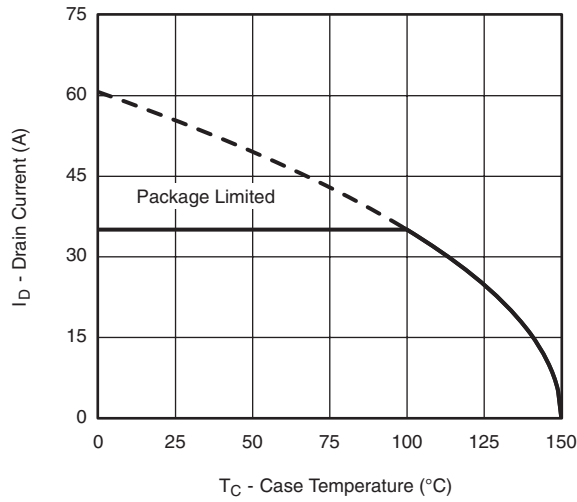
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

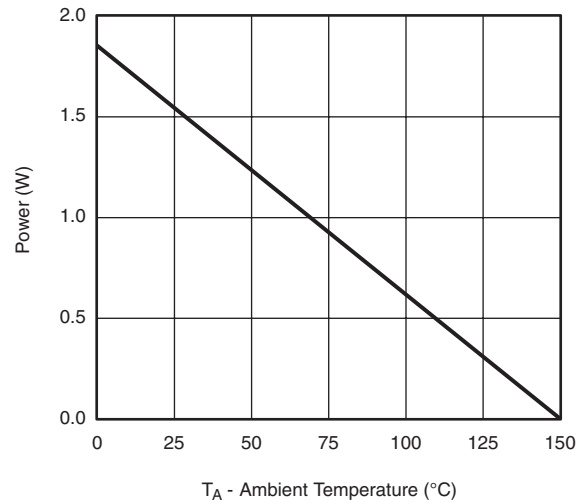


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



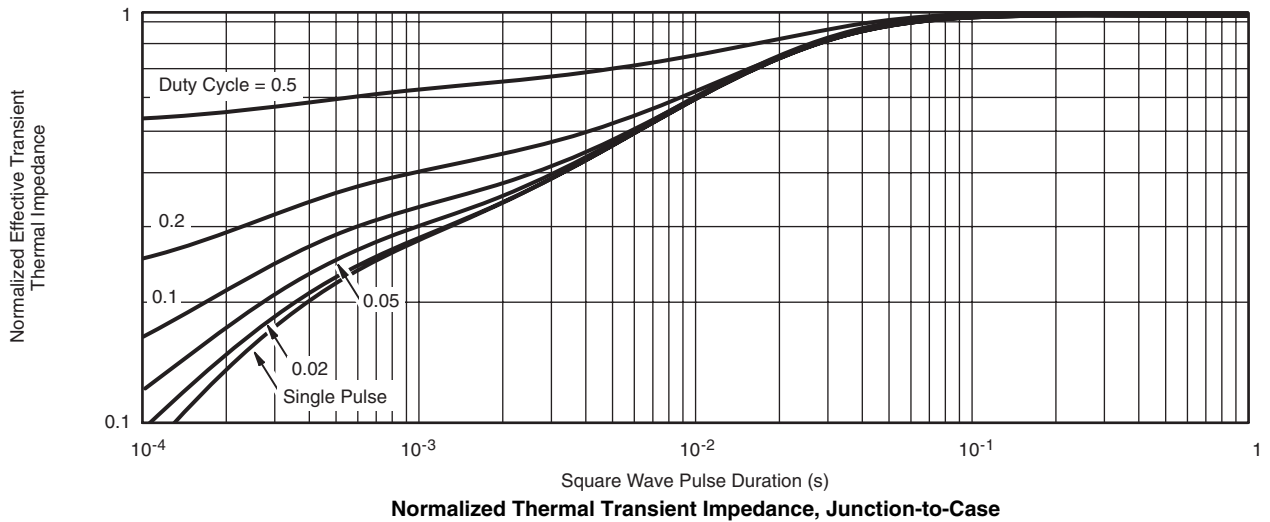
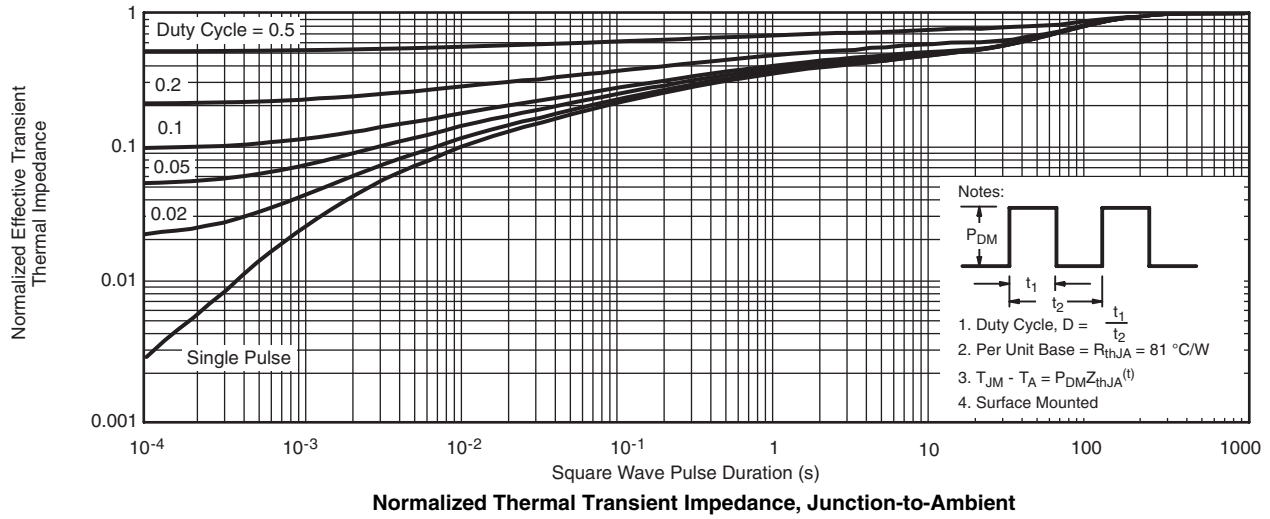
Current Derating*



Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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